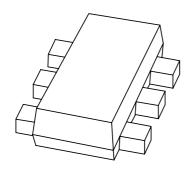
DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG1020EVUltra low V_F MEGA Schottky barrier rectifier

Product data sheet 2003 Jul 15



Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

FEATURES

Forward current: 2 AReverse voltage: 10 VUltra low forward voltage

· Ultra small plastic SMD package.

APPLICATIONS

Low voltage rectification

• High efficiency DC/DC conversion

• Switch mode power supply

· Inverse polarity protection

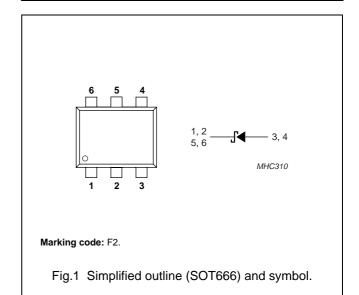
· Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in a SOT666 ultra small plastic SMD package.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | cathode |
| 2 | cathode |
| 3 | anode |
| 4 | anode |
| 5 | cathode |
| 6 | cathode |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|---|------|------|------|
| V_R | continuous reverse voltage | | _ | 10 | V |
| I _F | continuous forward current | T _{sp} ≤ 55 °C; note 1 | _ | 2 | А |
| I _{FRM} | repetitive peak forward current | $t_p \le 1$ ms; $\delta \le 0.5$; note 1 | _ | 3.2 | А |
| I _{FSM} | non-repetitive peak forward current | t _p = 8 ms square wave; note 1 | _ | 9 | А |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Only valid if pins 3 and 4 are connected in parallel.

2003 Jul 15 2

Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|-------------------|--|------|------|------|
| V _F | forward voltage | see Fig.2; note 1 | | | |
| | | I _F = 0.01 A | 100 | 130 | mV |
| | | I _F = 0.1 A | 164 | 200 | mV |
| | | I _F = 1 A | 255 | 350 | mV |
| | | I _F = 2 A | 306 | 460 | mV |
| I_R | reverse current | see Fig.3 note 2 | | | |
| | | V _R = 5 V | 0.7 | 2 | mA |
| | | V _R = 8 V | 1 | 2.5 | mA |
| | | V _R = 10 V | 1.2 | 3 | mA |
| C _d | diode capacitance | $V_R = 5 \text{ V}$; f = 1 MHz; see Fig.4 | 37 | 45 | pF |

Notes

- 1. Pulse test: $t_p = 300 \ \mu s$; $\delta = 0.02$.
- For Schottky barrier rectifiers thermal runaway has to be considered, as in some applications the reverse power losses (P_R) are a significant part of the total power losses.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|--|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 405 | K/W |
| | | note 2 | 215 | K/W |
| R _{th j-s} | thermal resistance from junction to solder point | note 3 | 80 | K/W |

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for cathode 1 cm².
- 3. Solder point of cathode tabs.

Soldering

Reflow soldering is the only recommended soldering method.

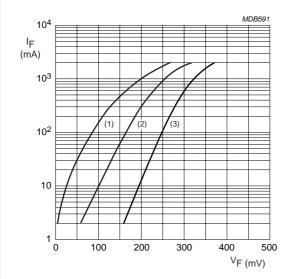
2003 Jul 15 3

Product data sheet **NXP Semiconductors**

Ultra low V_F MEGA Schottky barrier rectifier

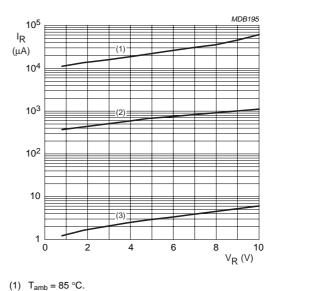
PMEG1020EV

GRAPHICAL DATA



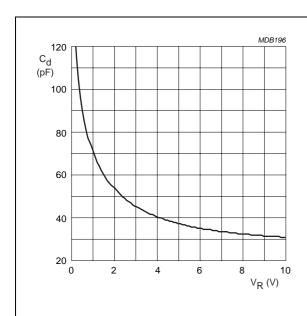
- (1) $T_{amb} = 85 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; $T_{amb} = 25 \,^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

2003 Jul 15 4

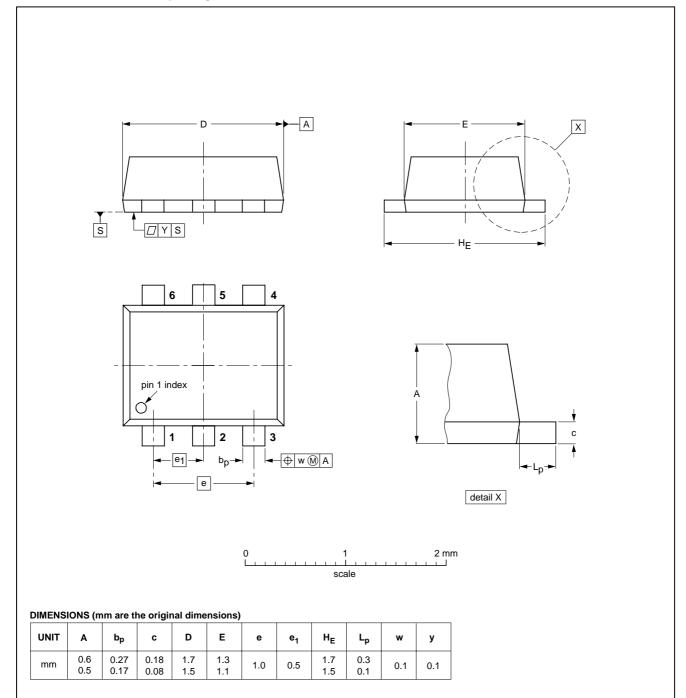
Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



REFERENCES

EIAJ

JEDEC

EUROPEAN

PROJECTION

ISSUE DATE

01-01-04 01-08-27

2003 Jul 15 5

IEC

OUTLINE VERSION

SOT666

Ultra low V_F MEGA Schottky barrier rectifier

PMEG1020EV

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

2003 Jul 15 6

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

Contact information

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands 613514/01/pp7 Date of release: 2003 Jul 15 Document order number: 9397 750 11686

